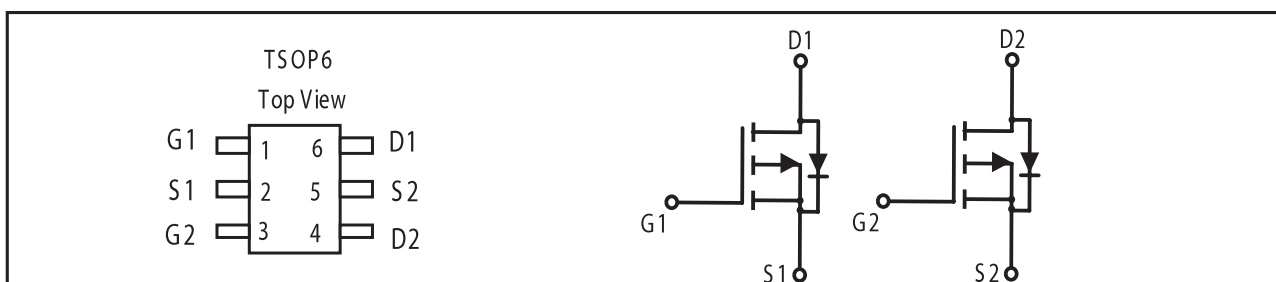


PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) MAX
-20V	-2A	130 @ V <sub>GS</sub> = -4.5V
		190 @ V <sub>GS</sub> = -2.5V

### FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- SOT-26 Package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Drain Current-Continuous <sup>a</sup> @ T <sub>C</sub> =25°C -Pulsed <sup>b</sup>	I <sub>D</sub>	-2	A
	I <sub>DM</sub>	-7	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	-1.25	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	1	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R <sub>θJA</sub>	125	°C/W
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